

TMG50H04DF

N+N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

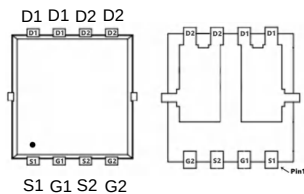
General Features

$V_{DS} = 40V$ $I_D = 50A$

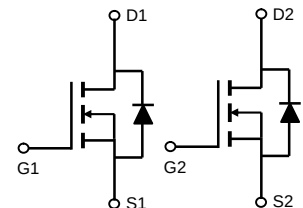
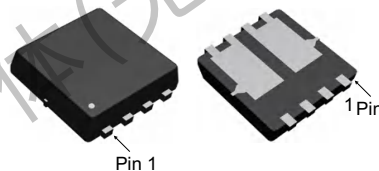
$R_{DS(ON)} = 7.2m\Omega$ (Typ.) @ $V_{GS} = 10V$

100% UIS Tested

100% R_g Tested



DF:DFN3x3-8L



Marking:50H04 OR 4896

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	32	A
I_{DM}	Pulsed Drain Current ²	198	A
EAS	Single Pulse Avalanche Energy ³	26.1	mJ
I_{AS}	Avalanche Current	15	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	43.6	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	5.4	$^\circ C/W$

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=12A$	---	7.2	9.5	$m\Omega$
		$V_{GS}=4.5V, I_D=10A$	---	9.6	12	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=20V, V_{GS}=4.5V, I_D=12A$	---	5.8	---	nC
Q_{gs}	Gate-Source Charge		---	3	---	
Q_{gd}	Gate-Drain Charge		---	1.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=1A$	---	14.3	---	ns
T_r	Rise Time		---	5.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	20	---	
T_f	Fall Time		---	11	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	660	---	pF
C_{oss}	Output Capacitance		---	193	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	50	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=31A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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Typical Characteristics

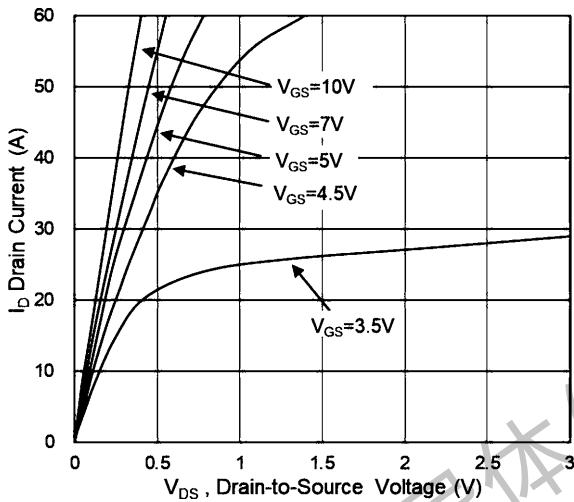


Fig.1 Typical Output Characteristics

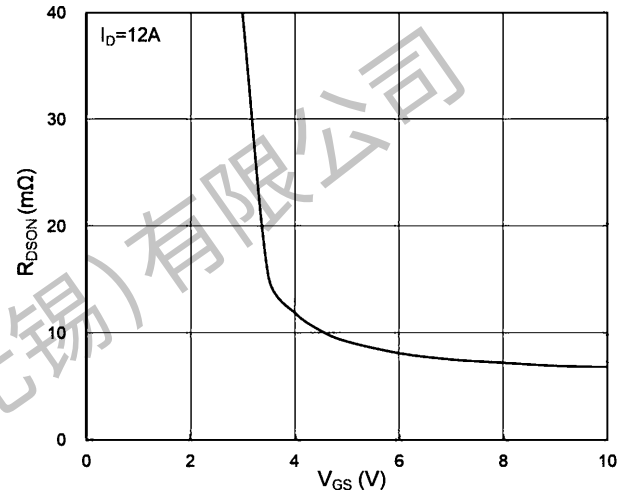


Fig.2 On-Resistance vs G-S Voltage

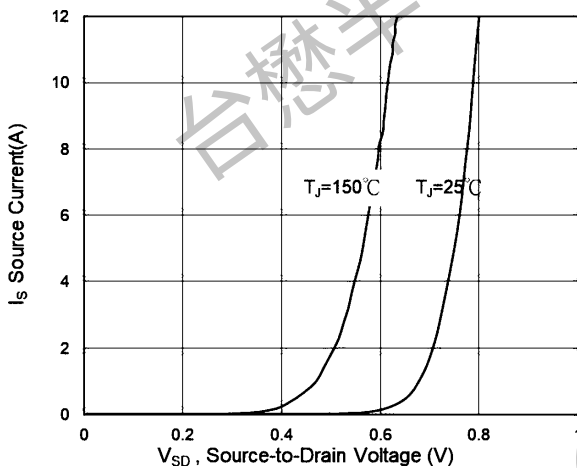


Fig.3 Source Drain Forward Characteristics

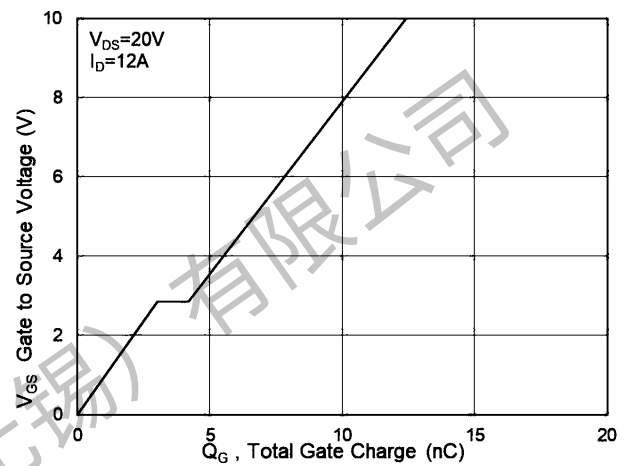


Fig.4 Gate-Charge Characteristics

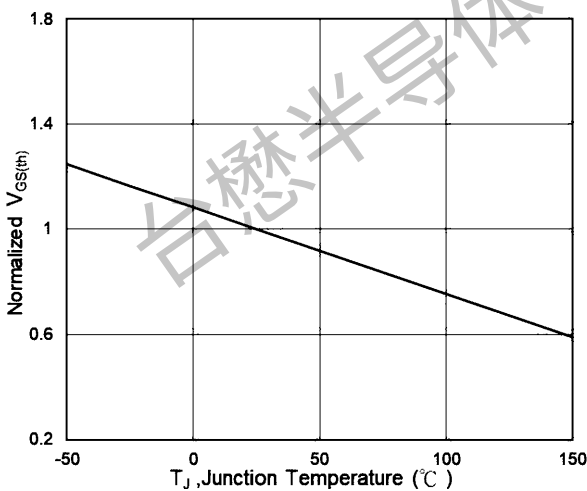


Fig.5 Normalized $V_{GS(th)}$ vs T_J

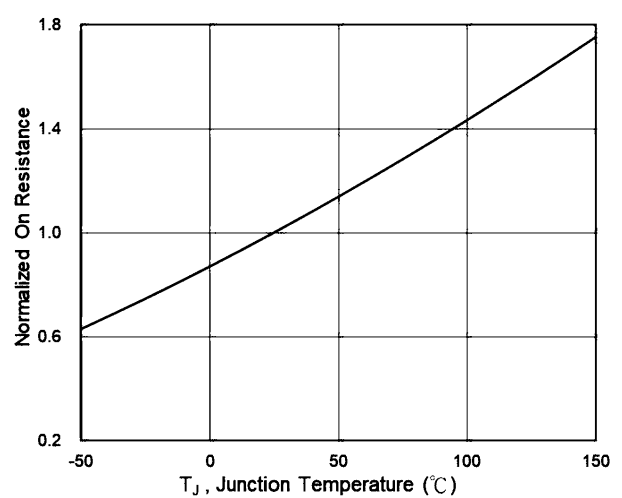


Fig.6 Normalized $R_{DS(on)}$ vs T_J

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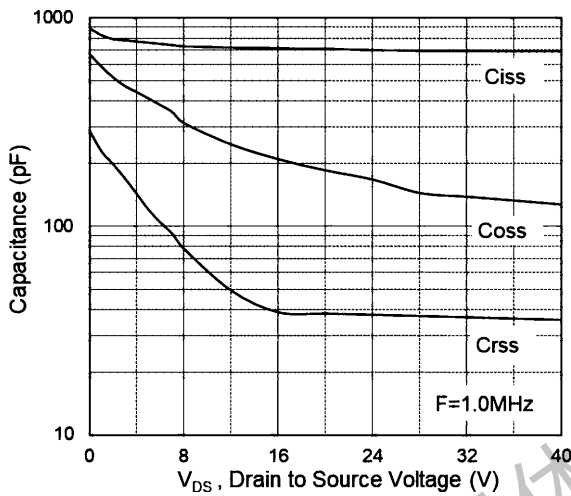


Fig.7 Capacitance

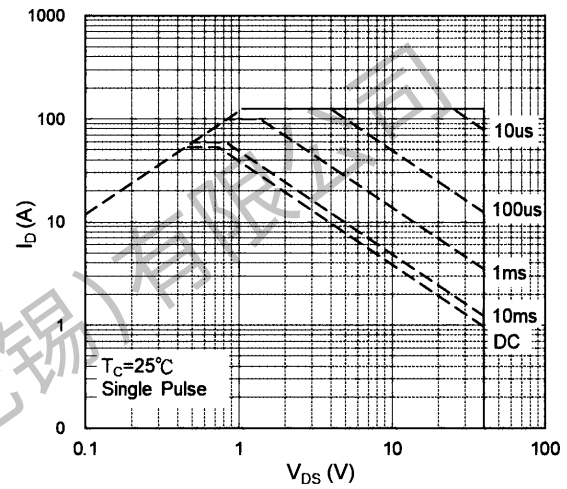


Fig.8 Safe Operating Area

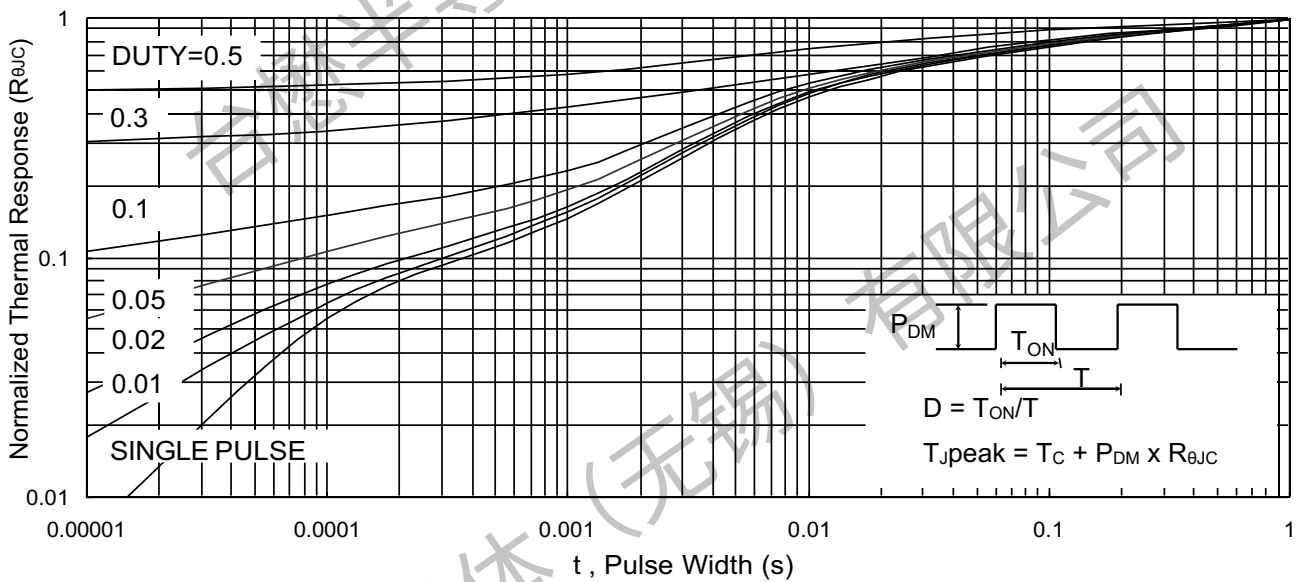
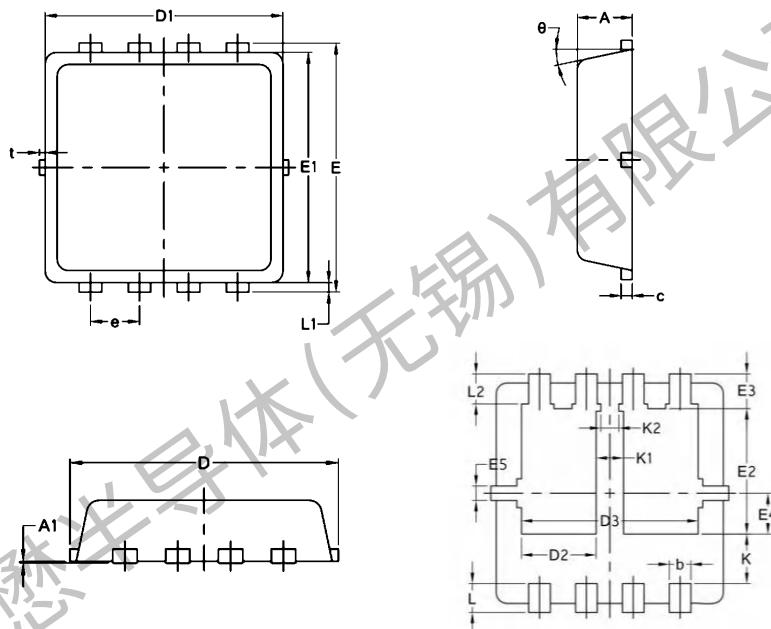


Fig.9 Normalized Maximum Transient Thermal Impedance

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Package Mechanical Data:DFN3x3-8L

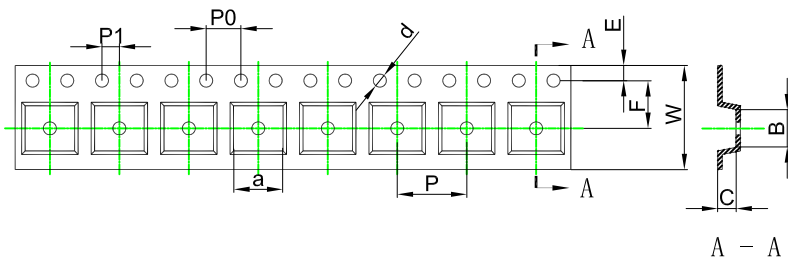


Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°

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PDFN3×3-8L Embossed Carrier Tape



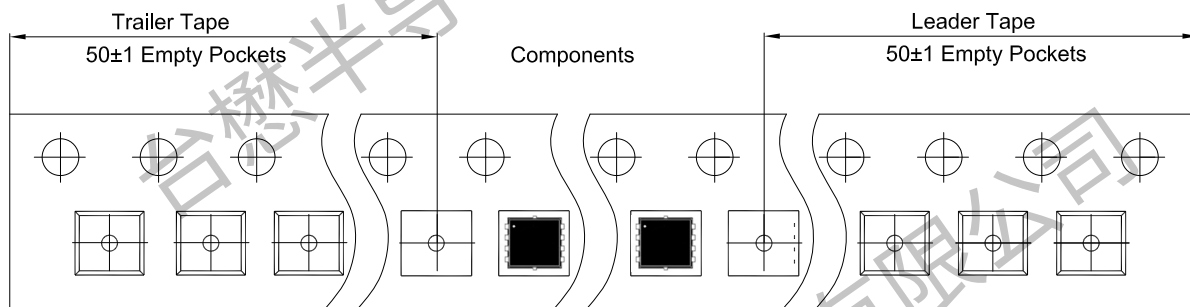
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

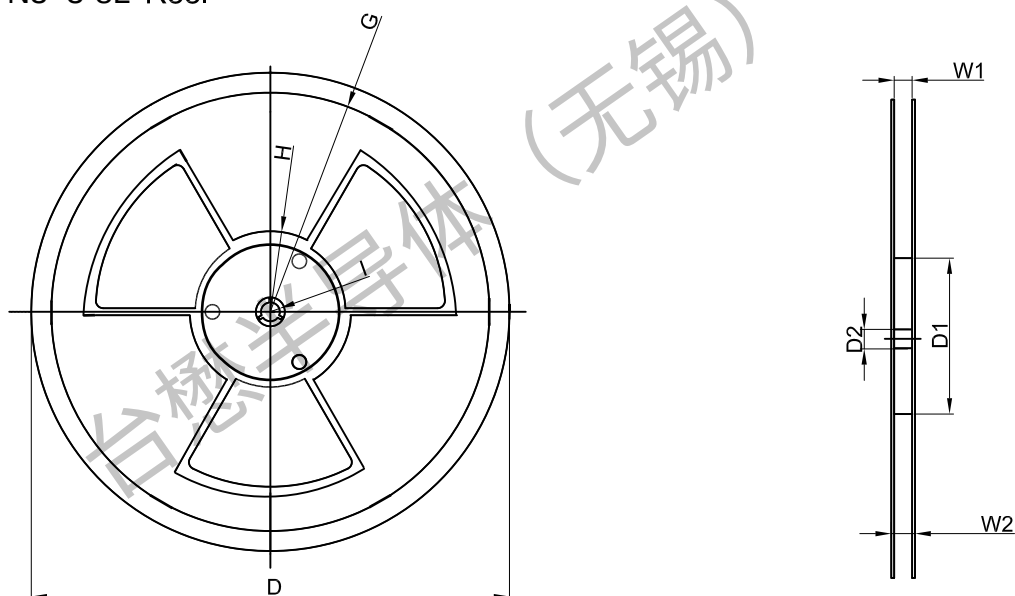
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN3×3-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN3×3-8L Tape Leader and Trailer



PDFN3×3-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2023.05.14	23.05	Original	